



## Low Power, Omnipolar, Hall Switch

### Data Sheet Rev. 1.1

#### 1. General

#### **Descriptions**

P4248 is a Hall-effect sensor integrated circuit of omni-polar switch type. It includes a hall plate, an amplifier with dynamic offset cancellation, a voltage regulator for operation with supply voltage from 1.8V to 5.5V, a sleep/awake control logic for low power consumption, schmitt trigger comparator, and a push-pull output. The offset cancellation reduces the offset voltage normally caused by device over molding, temperature dependencies, and thermal stress. The device is a temperature stable, stress-resistant sensor

P4248 detects magnetic field which is perpendicular to the package in an arbitrary direction. When the magnetic increases higher than Bop, the voltage of OUT goes low; when the magnetic decreases lower than BRP, OUT becomes high. When combined with a magnet, it becomes a non-contact switch with low current consumption, high sensitivity and reliability.

The device is delivered in a Small Outline Transistor (SOT23-3L) for surface mount process and in a Plastic Single In Line (TO92S) for through hole mount. The device is also delivered in small size SOT553 which package size is 1.6mm×1.2mm×0.6mm. All packages are RoHS compliant and Halogen Free.

#### **Features**

☐ High sensitivity: BOP=+/-30 Gauss, BRP=+/-20Gaus
□1.8~5.5V operating supply voltage
□ 5uA operating current at 1.8V
☐ Ambient temp range:-40C~85C
☐ >4KV ESD capability
☐ Push-pull output
☐ RoHS compliant 2011/65/EU and Halogen Free
□ Package: SOT23-3L/TO92S/SOT553
Typical Applications
☐ Solid-state switch
☐ Position detection
☐ Speed detection
□ Proximity detection



## **Package and Pin Description**



Figure 1. Package figure (not to scale)

Table 1(a): SOT23 Pin Description

I	SOT23 pin No.	Name	Description
	1	VDD	Power supply
	2	OUT	Output
	3	GND	Ground

Table 1(b): TO92S Pin Description

TO92S PIN NO.	Name	Description
1	VDD	Power supply
3	OUT	Output
2	GND	Ground

Table 1(C): DFN6L Pin Description

SOT553 PIN NO.	Name	Description
1	NC	Floating
2	GND	Ground
3	NC	Floating
4	VDD	Power supply
5	OUT	Output

Note: The NC pins can be floating or connected to GND

# 2. Ordering information

Table 2: Ordering information

No.	1	2	3	4	5		6~7
ON	Р	4	2	4	8	-	ST
							Deliver type
Description		Р	art No	).			UA: TO92S SO: SOT23-3L
							ST: SOT553



# 2. Block Diagram

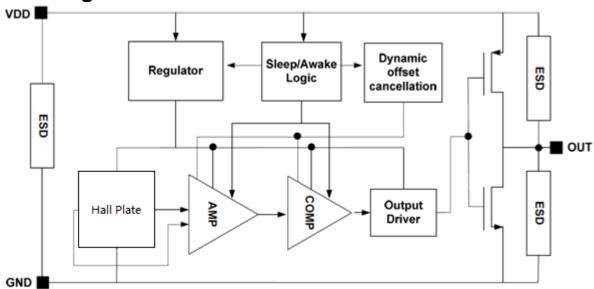


Figure 2: Functional Block Diagram

# 3. Function Description and Diagram of Operating

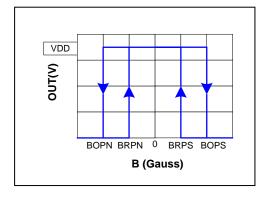


Figure 3: OUT VS Magnetic Field

### Diagram of operating to detect the magnetic



Figure 4: Magnetic detection diragram



# 4. Absolute Maximum Rating (Note1)

Table3: Absolute maximum rating (Ta=25C)

Symbol	Parameter	Min	Max	Unit
Vdd	Supply Voltage	-0.3	6.5	V
Idd	Supply Current	-	50	mA
Vout	Output Voltage	-0.3	6.5	V
lout	Output Current	-	1	mA
В	Magnetic Flux Density	Not lir	nited	Gauss
Ts	Storage Temp	-40	125	°C

Note 1: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. "Absolute Maximum Ratings" for extended period may affect device reliability.

## 5. Electrical Characteristics

Table 4: Electrical Characteristics (VDD=1.8V, Ta=25°C unless otherwise specified)

Symbol	Parameter	Condition	Min.	Тур.	Max.	Unit
Vdd	Supply voltage		1.8		5.5	V
Та	Ambient temperature range		-40		85	°C
ldd	Operating current		-	5.0	10.0	uA
Vol	Output low voltage	B > Bop , lout=0.5mA	-	-	0.2	V
Voh	Output high voltage	B < Brp , lout=0.5mA	VDD-0.2	-	-	V
loff	Output leakage current	VDD=5.5V,  B < Brp	-	0.1	10	uA
Тро	Power on time				100	uS
ESD		HBM		4		ΚV
Rth	Thermal resistance	SOT23-3L package		301		°C/W
Taw	Awake time			40	80	uS
Tsl	Sleep time			40	80	mS
D.C.	Duty cycle			0.1		%

# 6. Magnetic Characteristic

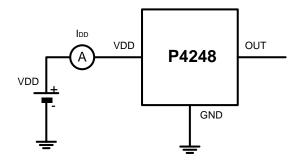
Table5: Magnetic Characteristic (VDD=1.8V)

Symbol	Parameter	Condition	Min.	Тур.	Max.	Unit
Вор	Operating point		+/-20	+/-30	+/-50	Gauss
Brp	Release point	Ta=25°C	+/-10	+/-20	+/-40	Gauss
Bhy	Hysteresis,  Bop-Brp		ı	10	-	Gauss



## 7. Test Diagram

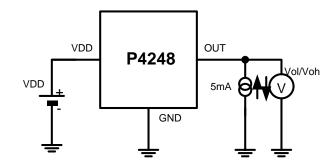
#### **Supply Current**



Note1- The supply current IDD represents the static supply current. Out is left open when measurement

Figure 5: Test diagram of Idd

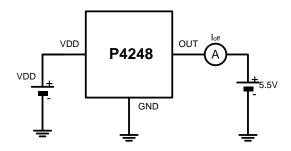
#### **Output Saturation Voltage**



Note1-Vol, |B|>30Gauss, 0.5mA lout is pushed into OUT pin. Note2- Voh, |B|=0Gauss, 0.5mA lout is pulled from OUT pin

Figure 6: Test diagram of Vol/Voh

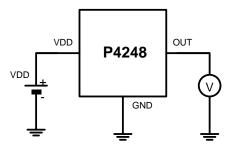
#### **Output Leakage Current**



Note1- The device is put under magnetic field with B<Brp

Figure 7: Test diagram of loff

#### **Magnetic Thresholds**



Note1- Bop is determined by putting the device under magnetic field swept from Brpmin up to Bopmax until the output is switch on Note2- Brp is determined by putting the device under magnetic field swept from Bopmax down to Brpmin until the output is switch off

Figure 8: Test diagram of magnetic thresholds



# 8. Typical Application

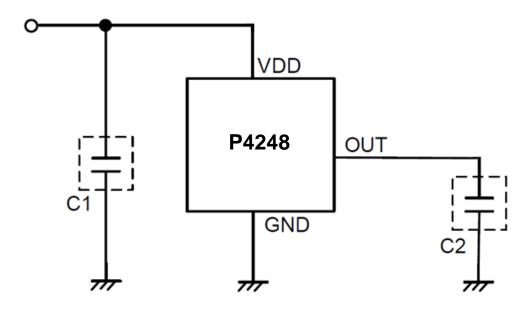


Figure 9: Typical Application Circuit

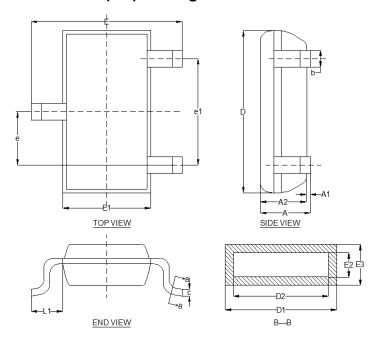
#### Note:

- 1. C1 is optional. Recommended value is 100nF to 1uF.
- 2. C2 is optional. Recommended value is 1nF to 100nF.



# 10. Package Information

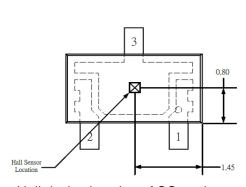
## 10.1 SOT23-3L(SO) Package size



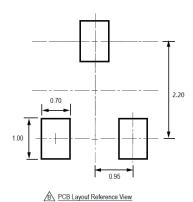
Combal	millimeters					
Symbol	M in	Тур	Max			
Α	-	-	1.100			
A1	0.025	0.075	0.100			
A2	0.850	0.880	0.900			
С	0.080	-	0.200			
D		0.290BSC				
D1	0.300	-	0.450			
D2	0.250	0.350	0.400			
Е	2.780BSC					
E1		1.600BSC				
E2	0.120	0.127	0.150			
E3	0.150	-	0.200			
е		0.950BSC				
e1	1.900BSC					
L1		0.600REF				
b	0.300	-	0.450			

Note: 1. Dimensions are not to scale

Figure 10: Package size of SO package



Hall device location of SO package



Recommended PCB layout information



## 10.2 TO92S (UA) Package size(Unit: mm)

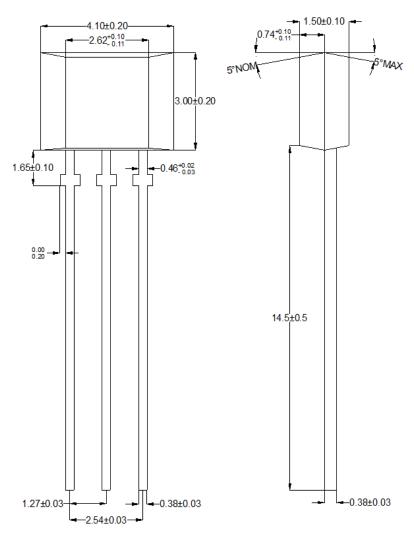


Figure 11: Package size of UA package

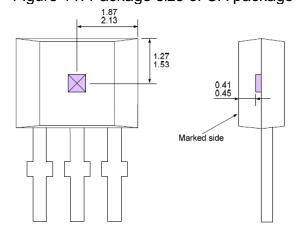
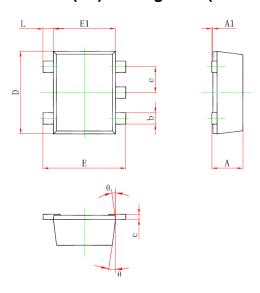


Figure 12: Hall device location of UA package



## 10.3 SOT553 (ST) Package size(Unit: mm)



Symbo <b>l</b>	Dimensions I	n Millimeters	Dimension	s In Inches	
Symbol	MIn.	Max.	MIn.	Max.	
A	0. 525	0.600	0.021	0.024	
A1	0.000	0.050	0.000	0.002	
e	0. 450	0.550	0.018	0.022	
c	0.090	0.160	0.004	0.006	
D	1. 500	1.700	0.059	0.067	
b	0. 170	0. 270	0.007	0.011	
E1	1. 100	1.300	0.043	0.051	
Е	1. 500	1.700	0.059	0.067	
L	0. 100	0.300	0.004	0.012	
θ	7 °I	REF.	7 °REF.		

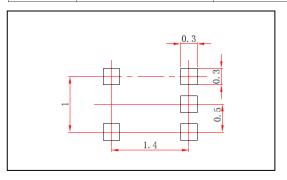


Figure 13: Package size of ST package

### **Sensor location**

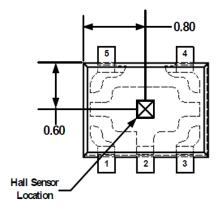


Figure 14: ST sensor location



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